National Semiconductor

74LCX841
Low-Voltage 10-Bit Transparent Latch with 5V Tolerant Inputs and Outputs

General Description

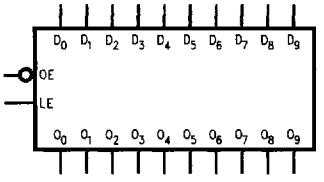
The LCX841 consists of ten latches with TRI-STATE® outputs for bus organized system applications. The device is designed for low voltage (3.3V) V_{CC} applications with capability of interfacing to a 5V signal environment.

The LCX841 is fabricated with an advanced CMOS technology to achieve high speed operation while maintaining CMOS low power dissipation.

Features

- 5V tolerant inputs and outputs
- 8.0 ns t_{PD} max, 10 μA I_{CCQ} max
- Power-down high impedance inputs and outputs
- Support live insertion/withdrawal
- 2.0V–3.6V V_{CC} supply operation
- ±24 mA output drive
- Implements patented Quiet Series™ noise/EMI reduction circuitry
- Functionally compatible with the 74 series 841
- *Latch-up performance exceeds 500 mA*
- ESD performance:
  Human Body Model > 2000V
  Machine Model > 200V

Logic Symbols



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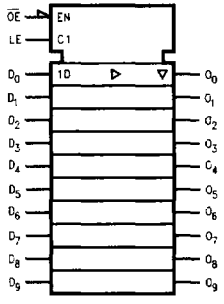
IEEE/IEC



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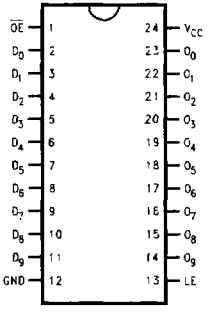
Connection Diagram

Pin Assignment for SOIC, SSOP and TSSOP



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Pin Names	Description
D_0–D_9	Data Inputs
LE	Latch Enable Input
$\overline{OE}$	Output Enable Input
O_0–O_9	TRI-STATE Latch Outputs

	SOIC JEDEC	SSOP Type II	TSSOP JEDEC
Order Number	74LCX841WM 74LCX841WMX	74LCX841MSA 74LCX841MSAX	74LCX841MTC 74LCX841MTCX
See NS Package Number	M24B	MSA24	MTC24

Functional Description

The LCX841 consists of ten D-type latches with TRI-STATE outputs. The flip-flops appear transparent to the data when *Latch Enable (LE) is HIGH. This allows asynchronous operation*, as the output transition follows the data in transition.

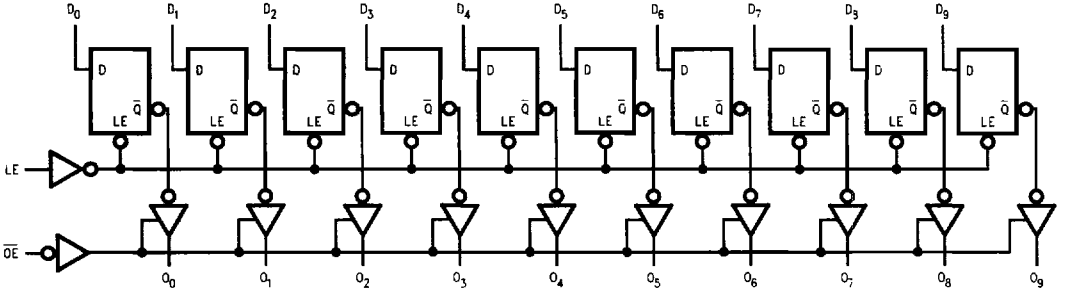
On the LE HIGH-to-LOW transition, the data that meets the setup and hold time is latched. Data appears on the bus when the Output Enable ($\overline{OE}$) is LOW. When $\overline{OE}$ is HIGH the bus output is in the high impedance state.

Function Table

Inputs			Internal	Output	Function
$\overline{OE}$	LE	D	Q	O	
X	X	X	X	Z	High Z
H	H	L	L	Z	High Z
H	H	H	H	Z	High Z
H	L	X	NC	Z	Latched
L	H	L	L	L	Transparent
L	H	H	H	H	Transparent
L	L	X	NC	NC	Latched

H = HIGH Voltage Level
L = LOW Voltage Level
X = Immaterial
Z = High Impendance
NC = No Change

Logic Diagram



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Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Symbol	Parameter	Value	Conditions	Units
V_{CC}	Supply Voltage	−0.5 to +7.0		V
V_I	DC Input Voltage	−0.5 to +7.0		V
V_O	DC Output Voltage	−0.5 to +7.0	Output in TRI-STATE	V
		−0.5 to V_{CC} + 0.5	Output in High or Low State (Note 2)	V
I_{IK}	DC Input Diode Current	−50	V_I < GND	mA
I_{OK}	DC Output Diode Current	−50 +50	V_O < GND V_O > V_{CC}	mA
I_O	DC Output Source/Sink Current	±50		mA
I_{CC}	DC Supply Current per Supply Pin	±100		mA
I_{GND}	DC Ground Current per Ground Pin	±100		mA
T_{STG}	Storage Temperature	−65 to +150		°C

Note 1: *The Absolute Maximum Ratings are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the Absolute Maximum Ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.*

Note 2: I_O Absolute Maximum Rating must be observed.

Recommended Operating Conditions

Symbol	Parameter		Min	Max	Units
V_{CC}	Supply Voltage	Operating Data Retention	2.0 1.5	3.6 3.6	V
V_I	Input Voltage		0	5.5	V
V_O	Output Voltage	HIGH or LOW State TRI-STATE	0 0	V_{CC} 5.5	V
I_{OH}/I_{OL}	Output Current	V_{CC} = 3.0V–3.6V V_{CC} = 2.7V		±24 ±12	mA
T_A	Free-Air Operating Temperature		−40	85	°C
$\Delta t/\Delta V$	Input Edge Rate, V_{IN} = 0.8V–2.0V, V_{CC} = 3.0V		0	10	ns/V

DC Electrical Characteristics

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = −40°C to +85°C		Units
				Min	Max	
V_{IH}	HIGH Level Input Voltage		2.7–3.6	2.0		V
V_{IL}	LOW Level Input Voltage		2.7–3.6		0.8	V
V_{OH}	HIGH Level Output Voltage	I_{OH} = −100 μA	2.7–3.6	V_{CC} − 0.2		V
		I_{OH} = −12 mA	2.7	2.2		V
		I_{OH} = −18 mA	3.0	2.4		V
		I_{OH} = −24 mA	3.0	2.2		V
V_{OL}	LOW Level Output Voltage	I_{OL} = 100 μA	2.7–3.6		0.2	V
		I_{OL} = 12 mA	2.7		0.4	V
		I_{OL} = 16 mA	3.0		0.4	V
		I_{OL} = 24 mA	3.0		0.55	V
I_I	Input Leakage Current	0 ≤ V_I ≤ 5.5V	2.7–3.6		±5.0	μA
I_{OZ}	TRI-STATE Output Leakage	0 ≤ V_O ≤ 5.5V V_I = V_{IH} or V_{IL}	2.7–3.6		±5.0	μA
I_{OFF}	Power-Off Leakage Current	V_I or V_O = 5.5V	0		10	μA
I_{CC}	Quiescent Supply Current	V_I = V_{CC} or GND	2.7–3.6		10	μA
		3.6V ≤ V_I, V_O ≤ 5.5V	2.7–3.6		±10	μA
ΔI_{CC}	Increase in I_{CC} per Input	V_{IH} = V_{CC} − 0.6V	2.7–3.6		500	μA

AC Electrical Characteristics

Symbol	Parameter	$T_A = -40°C$ to $+85°C$				Units
		$V_{CC} = 3.3V \pm 0.3V$		$V_{CC} = 2.7V$		
		Min	Max (Note 1)	Min	Max Note 1	
t_{PHL} t_{PLH}	Propagation Delay D_n to O_n	1.5 1.5	7.0 7.0	1.5 1.5	7.5 7.5	ns
t_{PHL} t_{PLH}	Propagation Delay LE to O_n	1.5 1.5	7.0 7.0	1.5 1.5	7.5 7.5	ns
t_{PZL} t_{PZH}	Output Enable Time	1.5 1.5	8.0 8.0	1.5 1.5	8.5 8.5	ns
t_{PLZ} t_{PHZ}	Output Disable Time	1.5 1.5	6.5 6.5	1.5 1.5	7.0 7.0	ns
t_{OSHL} t_{OSLH}	Output to Output Skew (Note 2)		1.0 1.0			ns
t_S	Setup Time D_n to LE	2.5		2.5		ns
t_H	Hold Time D_n to LE	1.5		1.5		ns
t_W	LE Pulse Width	3.3		3.3		ns

Note 1: The Maximum AC limits are design target. Actual performance will be specified upon completion of characterization.

Note 2: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The *specification applies to any outputs switching in the same direction, either HIGH to LOW (t_{OSHL}) or LOW to HIGH (t_{OSLH}).*

Dynamic Switching Characteristics

Symbol	Parameter	Conditions	V_{CC} (V)	$T_A = 25°C$ Typical	Units
V_{OLP}	Quiet Output Dynamic Peak V_{OL}	$C_L = 50$ pF, $V_{IH} = 3.3V$, $V_{IL} = 0V$	3.3	0.8	V
V_{OLV}	Quiet Output Dynamic Valley V_{OL}	$C_L = 50$ pF, $V_{IH} = 3.3V$, $V_{IL} = 0V$	3.3	−0.8	V

Capacitance

Symbol	Parameter	Conditions	Typical	Units
C_{IN}	Input Capacitance	V_{CC} = Open, $V_I = 0V$ or V_{CC}	7	pF
C_O	Output Capacitance	$V_{CC} = 3.3V$, $V_I = 0V$ or V_{CC}	8	pF
C_{PD}	Power Dissipation Capacitance	$V_{CC} = 3.3V$, $V_I = 0V$ or V_{CC}, f = 10 MHz	20	pF